

L Number	Hits	Search Text	DB	Time stamp
13	3381	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.	USPAT; US-PGPUB	2004/04/15 13:50
14	743	LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor"	USPAT; US-PGPUB	2004/04/15 13:51
15	1416	RSD or "reduced surface drain" or "reduced-surface-drain"	USPAT; US-PGPUB	2004/04/15 13:51
16	9	(LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain")	USPAT; US-PGPUB	2004/04/15 13:51
17	1	((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain"))	USPAT; US-PGPUB	2004/04/15 13:51
18	9	((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (RSD or "reduced surface drain" or "reduced-surface-drain")	USPAT; US-PGPUB	2004/04/15 13:55
19	34	((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor")	USPAT; US-PGPUB	2004/04/15 13:55
20	3404420	@ad<20010821	USPAT; US-PGPUB	2004/04/15 13:56
21	28	(((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor")) and @ad<20010821	USPAT; US-PGPUB	2004/04/15 14:05
23	1160	(implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates))	USPAT; US-PGPUB	2004/04/15 14:08

24	204	((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulations or oxide or oxides) with (gate or gates)))	USPAT; US-PGPUB	2004/04/15 14:09
25	1	(((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and (LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor")) and @ad<20010821) and (((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulations or oxide or oxides) with (gate or gates))))	USPAT; US-PGPUB	2004/04/15 14:10
26	911	((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulations or oxide or oxides) with (gate or gates))) and @ad<20010821	USPAT; US-PGPUB	2004/04/15 14:11
27	9	(RSD or "reduced surface drain" or "reduced-surface-drain") and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain"))	USPAT; US-PGPUB	2004/04/15 14:11
28	0	((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulations or oxide or oxides) with (gate or gates))) and @ad<20010821) and ((RSD or "reduced surface drain" or "reduced-surface-drain") and ((LDMOS or "lateral double diffused metal oxide semiconductor" or "lateral double-diffused metal oxide semiconductor" or "lateral-double-diffused-metal-oxide-semiconductor") and (RSD or "reduced surface drain" or "reduced-surface-drain"))))	USPAT; US-PGPUB	2004/04/15 14:11

29	173	@ad<20010821 and (((((438/301) or (438/302) or (438/303) or (438/304) or (438/305) or (438/306) or (438/307) or (438/920)).CCLS.) and ((implant or implants or implanted or implanting or implantation) with (heat or heats or heated or heating or anneal or anneals or annealed or annealing) with ((dielectric or dielectrics or insulating or insulating or oxide or oxides) with (gate or gates))))))	USPAT; US-PGPUB	2004/04/15 14:12
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